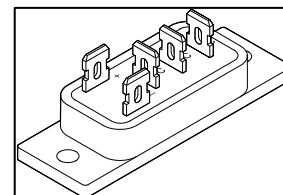


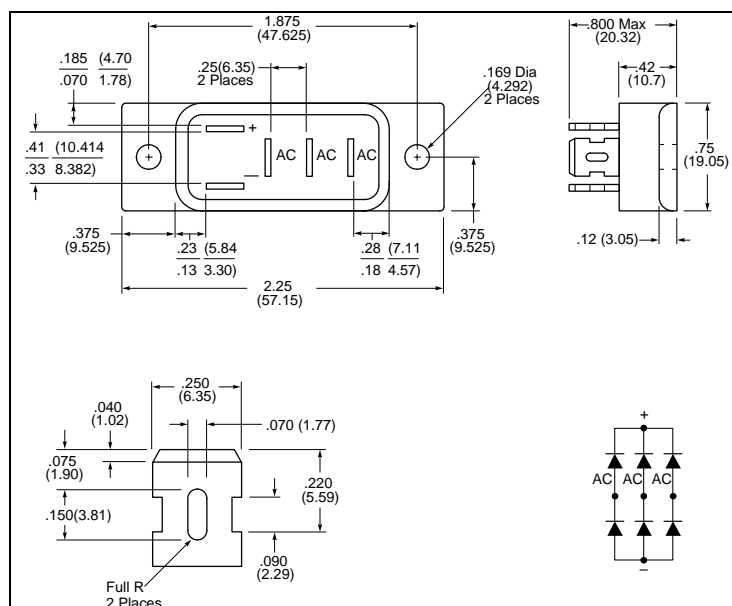
TECHNICAL DATA
DATA SHEET 900, REV -**THREE PHASE FULL WAVE
BRIDGE RECTIFIER ASSEMBLY****DESCRIPTION: A 400 VOLT, 25 AMP, 5000 NANOSECOND THREE PHASE BRIDGE RECTIFIER ASSEMBLY.****MAXIMUM RATINGS**All ratings are at $T_A = 25^{\circ}\text{C}$ unless otherwise specified.

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV)	-	-	-	400	Vdc
Average DC Output Current ($T_C = \text{Case Temp}$) (I_o)	$T_C = 55^{\circ}\text{C}$ $T_C = 100^{\circ}\text{C}$ $T_C = 125^{\circ}\text{C}$	-	-	25 18.5 12.5	Amps
Average DC Output Current Ambient Temp. (no heat sink) (I_o)	$T_A = 25^{\circ}\text{C}$ $T_A = 55^{\circ}\text{C}$ $T_A = 100^{\circ}\text{C}$	-	-	6.0 5.0 3.0	Amps
Peak Single Cycle Surge Current (I_{FSM})	$t_p = 8.3 \text{ ms}$ Single Half Cycle Sine Wave, Superimposed On Rated Load	-	-	150	Amps(pk)
Thermal Resistance (θ_{JL})	-	-	-	1.5	$^{\circ}\text{C/W}$
Operating and Storage Temp. (T_{op} & T_{stg})	-	-55	-	+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	CONDITIONS	MIN	TYP	MAX	UNIT
Maximum Forward Voltage (V_f)	$I_f = 9\text{A}$ (300 μsec pulse, duty cycle < 2%)	-	-	1.3	Volts
Maximum Instantaneous Reverse Current At Rated (PIV)	$T_A = 25^{\circ}\text{C}$ $T_A = 100^{\circ}\text{C}$	-	-	5.0 100	μAmps
Reverse Recovery Time (t_{rr})	$I_f = 0.5\text{A}$, $I_r = 1.0\text{A}$, $I_{rr} = 0.25\text{A}$	-	-	5000	nsec

SENSITRON

TECHNICAL DATA
DATA SHEET 900, REV. -
MECHANICAL DIMENSIONS: In Inches / mm

FIG. 404

Note: Case finish - Black Anodized

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